

ISL72991RH

Neutron Testing of the ISL72991RH Radiation Hardened Low Dropout Adjustable Negative Voltage Regulator

Introduction

This report summarizes results of 1MeV equivalent neutron testing of the [ISL72991RH](#) low dropout adjustable negative regulator. The test was conducted to determine the sensitivity of the part to Displacement Damage (DD) caused by neutron or proton environments. Neutron fluences ranged from $1 \times 10^{11} \text{ n/cm}^2$ to $1 \times 10^{14} \text{ n/cm}^2$. This project was carried out in collaboration with the Advanced Technology Laboratories Division of Northrop Grumman Corporation and their support is gratefully acknowledged.

Part Description

The radiation hardened ISL72991RH is a low dropout adjustable negative regulator with an output voltage range of -2.25V to -26V. The device features a 1A output current capability, an adjustable current limit pin (ILIM), and a shutdown pin (SD) for easy on/off control.

The ISL72991RH incorporates unique circuitry that enables precision performance across the -55°C to +125°C temperature range and post-irradiation. Specifications across the full temperature range include an internal reference voltage of -1.25V +40mV/-50mV (maximum), line regulation of $\pm 25\text{mV}$ (maximum), and load regulation of $\pm 15\text{mV}$ (maximum). The reference voltage is the ADJ to GND voltage.

Constructed with the Renesas dielectrically isolated Rad Hard Silicon Gate (RSG) BiCMOS process, these devices are immune to single event latch-up and have been specifically designed to provide highly reliable performance in harsh radiation environments.

Specifications for Rad Hard QML devices are controlled by the Defense Logistics Agency (DLA) in Columbus, OH. The SMD is the controlling document and must be cited when ordering.

Related Literature

For a full list of related documents, visit our website

- [ISL72991RH](#) product page
- MIL-STD-883 test method 1017

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1. Test Description

1.1 Irradiation Facility

Neutron fluence irradiations were performed on the test samples on June 25, 2015, at the WSMR Fast Burst Reactor (FBR) per MIL-STD-883G, Method 1017.2, with each part unpowered during irradiation and all leads shorted. The target irradiation levels were $1 \times 10^{11} \text{ n/cm}^2$, $5 \times 10^{11} \text{ n/cm}^2$, $1 \times 10^{12} \text{ n/cm}^2$, $1 \times 10^{12} \text{ n/cm}^2$, and $1 \times 10^{14} \text{ n/cm}^2$. As neutron irradiation activates many of the heavier elements found in a packaged integrated circuit, the parts exposed at the higher neutron levels required (as expected) some 'cooldown' time before being shipped back to the Renesas Palm Bay facility for electrical testing.

1.2 Test Fixturing

No formal irradiation test fixturing is involved, as these DD tests are 'bag tests' in the sense that the parts are irradiated with all leads shorted together.

1.3 Radiation Dosimetry

Table 1 shows the TLD and Sulfur pellet dosimetry from WSMR indicating the total accumulated gamma dose and actual neutron fluence exposure levels for each sets of samples. This dosimetry process is traceable to NIST (IAW ASTM E722).

Table 1. ISL72991RH Neutron Fluence Dosimetry Data

TLD		Sulfur Pellet						
TLD Number	cGy(Si) ^[1]	Pellet Number	Distance (inches)	Exposure ID	Flu >3MeV (n/cm ²)	% Unc ^[2]	Total Fluence (n/cm ²)	1Mev Si (n/cm ²)
81	2.760E+01	3263	49	Free Field	1.536E+10	7.1	1.335E+11	1.087E+11
82	1.315E+02	3264	21.65	Free Field	8.779E+10	7.1	7.016E+11	6.105E+11
83	5.403E+02	3265	11	Free Field	3.334E+11	7.1	2.620E+12	2.337E+12
85	2.954E+03	3267	31.15	Free Field	1.528E+12	7.1	1.253E+13	1.066E+13
84	2.997E+04	3266	10	Free Field	1.990E+13	7.1	1.562E+14	1.395E+14

1. $1 \text{ cGy(Si)} = 1 \text{ rad(Si)}$

2. The Uncertainty (% Unc) column is applicable only to the Fluence > 3MeV.

1.4 Characterization Equipment and Procedures

Electrical testing was performed before and after irradiation using the production Automated Test Equipment (ATE). All electrical testing was performed at room temperature.

1.5 Experimental Matrix

Testing proceeded in general accordance with the guidelines of MIL-STD-883 test method 1017. The experimental matrix consisted of ten samples irradiated at $1 \times 10^{11} \text{ n/cm}^2$, five samples irradiated at $5 \times 10^{11} \text{ n/cm}^2$, five irradiated at $1 \times 10^{12} \text{ n/cm}^2$, five irradiated at $1 \times 10^{13} \text{ n/cm}^2$, and five irradiated at $1 \times 10^{14} \text{ n/cm}^2$. Six control units were used.

ISL72991RH samples were drawn from Lot DD4T4CB. Samples were packaged in the standard hermetic 28 Ld Ceramic Flatpack (CFP) production package, code K28.A. Samples were processed through burn-in before irradiation and were screened to the SMD limits at room, low, and high temperatures before the start of neutron testing.

2. Results

Neutron testing of the ISL72991RH is complete and the results are reported in the balance of this report. It should be understood when interpreting the data that each neutron irradiation was performed on a different set of samples; this is *not* total dose testing, where the damage is cumulative.

2.1 Attributes Data

Table 2. Attributes Data

Fluence (n/cm ²)		Sample Size	Pass ^[1]	Fail
Planned	Actual			
1x10 ¹¹	1.1x10 ¹¹	10	10	0
5x10 ¹¹	6.1x10 ¹¹	5	5	0
1x10 ¹²	2.3x10 ¹²	5	5	0
1x10 ¹³	1.1x10 ¹³	5	5	0
1x10 ¹⁴	1.4x10 ¹⁴	5	0	5

1. A Pass indicates a sample that passes all SMD limits.

2.2 Variables Data

Figure 1 through Figure 11 show data plots for key parameters before and after irradiation to each level. The plots show the mean of each parameter as a function of neutron irradiation. Also, they include error bars at each datapoint, representing the minimum and maximum measured values of the samples, although in some plots the error bars might not be visible due to their values compared to the scale of the graph. The applicable electrical limits taken from the SMD are also shown.

All samples passed the post-irradiation SMD limits after all exposures up to and including 1x10¹³n/cm², but failed the SMD post-irradiation limits after 1x10¹⁴n/cm².

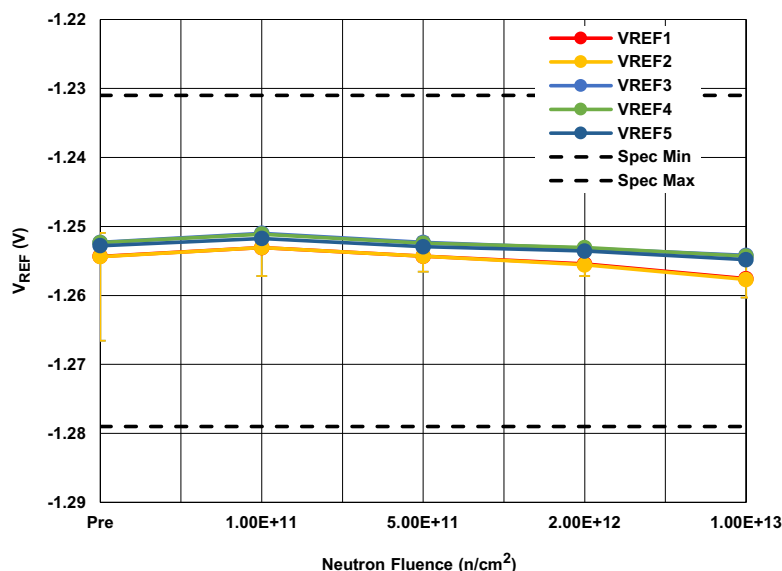


Figure 1. ISL72991RH reference voltage (V_{REF}) at five different conditions following irradiation to each level. Parts were non-functional after 1E14n/cm² and the results are not plotted. V_{REF1} denotes $V_{IN} = 30V$, no load, V_{REF2} denotes $V_{IN} = 30V$, 1A, V_{REF3} denotes $V_{IN} = 3.5V$, no load, V_{REF4} denotes $V_{IN} = 3.5V$, 1A, and V_{REF5} denotes $V_{IN} = 7V$, 1A. The error bars represent the minimum and maximum measured values. The SMD limits are -1.279V minimum and -1.231V maximum.

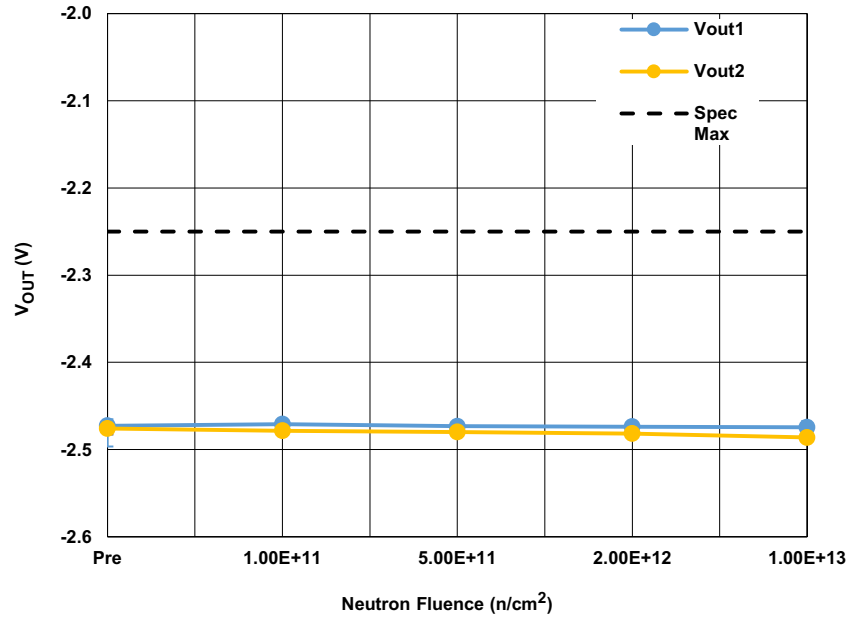


Figure 2. ISL72991RH minimum output voltage (V_{OUT}) with $V_{IN} = 3V$ at two different conditions following irradiation to each level. Parts were non-functional after $1E14n/cm^2$ and the results are not plotted. V_{OUT1} denotes a 10mA load, and V_{OUT2} denotes no load. The error bars represent the minimum and maximum measured values. The SMD limit is -2.25V maximum.

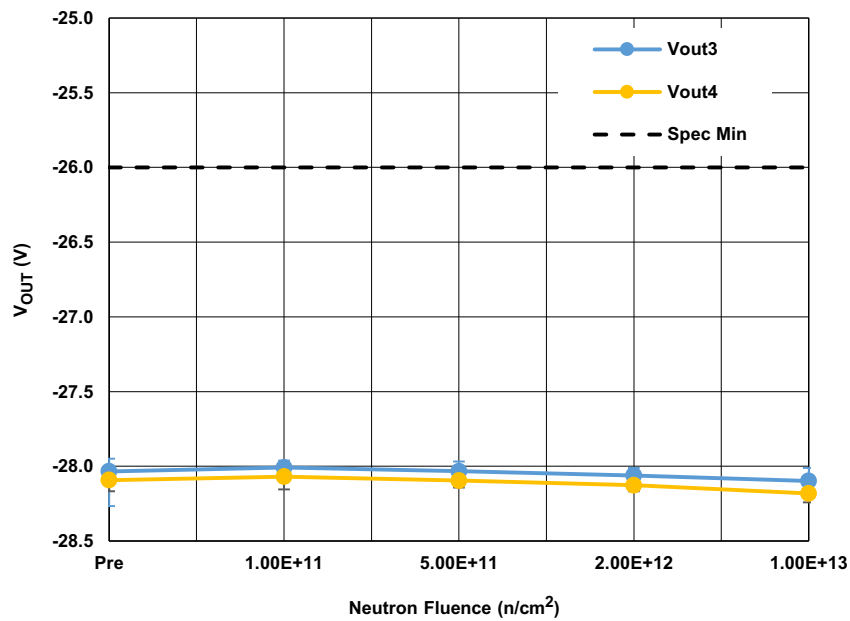


Figure 3. ISL72991RH maximum output voltage (V_{OUT}) with $V_{IN} = 30V$ at two different conditions following irradiation to each level. Parts were non-functional after $1E14n/cm^2$ and the results are not plotted. V_{OUT3} denotes a 10mA load, and V_{OUT4} denotes no load. The error bars represent the minimum and maximum measured values. The SMD limit is -26.0V maximum.

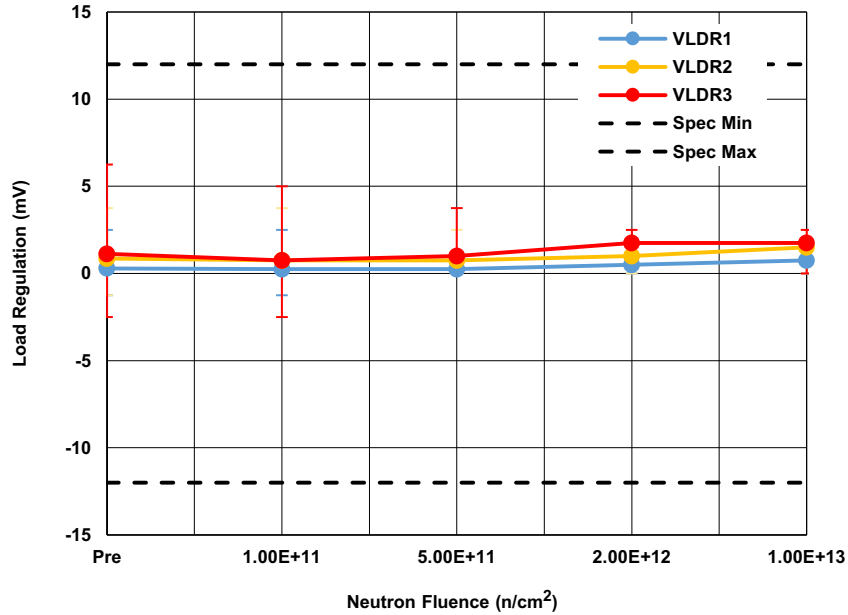


Figure 4. ISL72991RH load regulation (V_{LDR}) with $V_{IN} = -7V$, $V_O = -5V$, at three different conditions following irradiation to each level. Parts were non-functional after $1E14n/cm^2$ and the results are not plotted. V_{LDR1} denotes a 100mA load, V_{LDR2} denotes a 700mA load, and V_{LDR3} denotes a 1A load. The error bars represent the minimum and maximum measured values. The SMD limits are -12.0V minimum and 12.0V maximum.

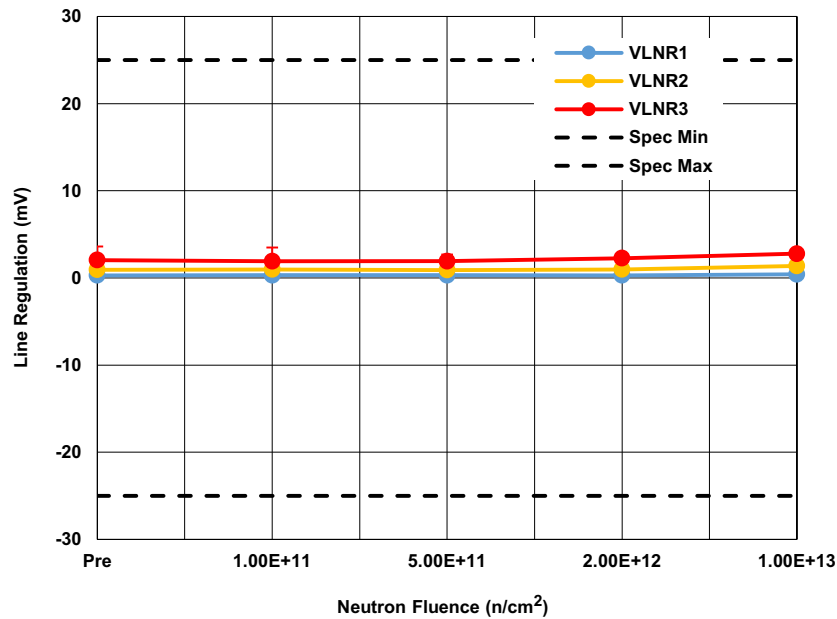


Figure 5. ISL72991RH line regulation (V_{LNR}) with $I_O = 100mA$ at three different conditions following irradiation to each level. Parts were non-functional after $1E14n/cm^2$ and the results are not plotted. V_{LNR1} denotes V_{OUT} at 4V - V_{OUT} at 7V, V_{LNR2} denotes V_{OUT} at 4V - V_{OUT} at 15V, and V_{LNR3} denotes V_{OUT} at 4V - V_{OUT} at 30V. The error bars represent the minimum and maximum measured values. The SMD limits are -25.0mV minimum and 25.0mV maximum.

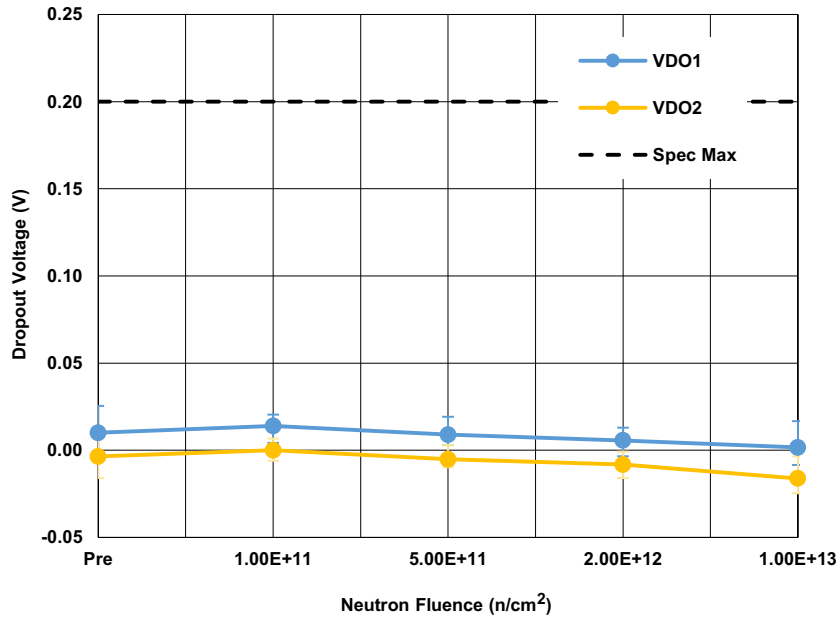


Figure 6. ISL72991RH dropout voltage (V_{DO}) at two different conditions following irradiation to each level. Parts were non-functional after $1E14n/cm^2$ and the results are not plotted. V_{DO1} denotes $I_O = 100mA$, and V_{DO2} denotes $I_O = 1A$. The error bars represent the minimum and maximum measured values. The SMD limit is 0.2V maximum for V_{DO1} and 1.0V maximum for V_{DO2} (not shown).

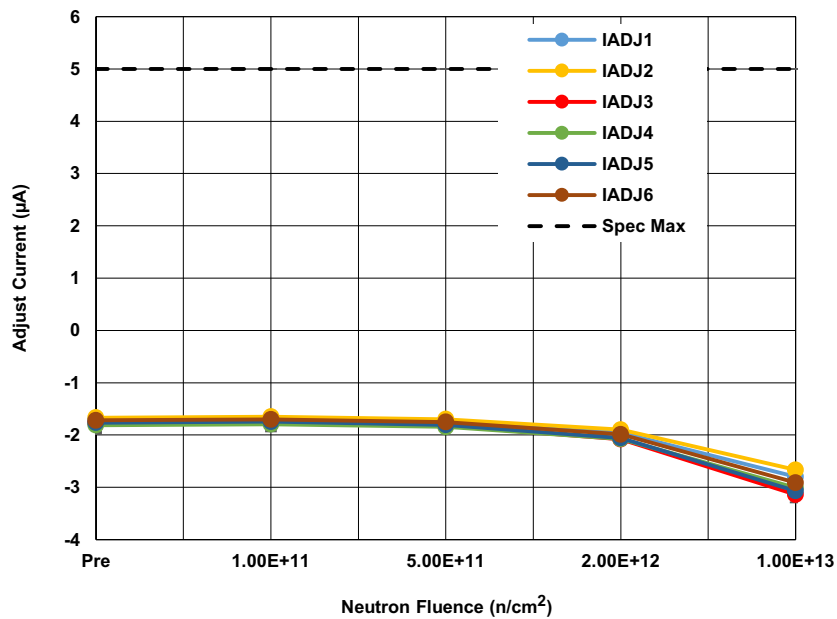


Figure 7. ISL72991RH adjust current (I_{ADJ}) at six different conditions following irradiation to each level. Parts were non-functional after $1E14n/cm^2$ and the results are not plotted. I_{ADJ1} denotes $V_{IN} = 30V$, no load, I_{ADJ2} denotes $V_{IN} = 30V$, 500mA, I_{ADJ3} denotes $V_{IN} = 4V$, no load, I_{ADJ4} denotes $V_{IN} = 4V$, 500mA, I_{ADJ5} denotes $V_{IN} = 7V$, no load, and I_{ADJ6} denotes $V_{IN} = 7V$, 500mA. The error bars represent the minimum and maximum measured values. The SMD limit is 5µA maximum.

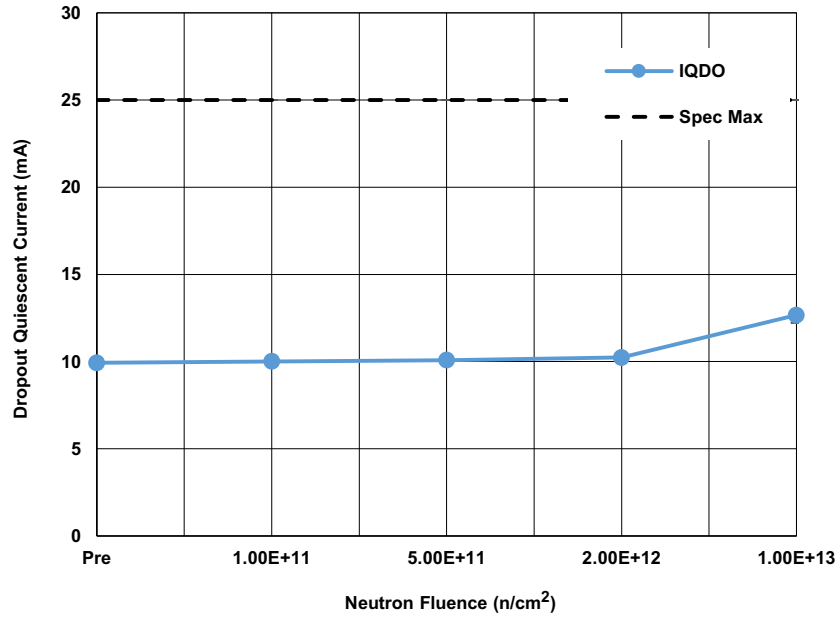


Figure 8. ISL72991RH dropout quiescent current (I_{QDO}) at $I_O = 500\text{mA}$ following irradiation to each level. Parts were non-functional after $1\text{E}14\text{n/cm}^2$ and the results are not plotted. The error bars represent the minimum and maximum measured values. The SMD limit is 25mA maximum.

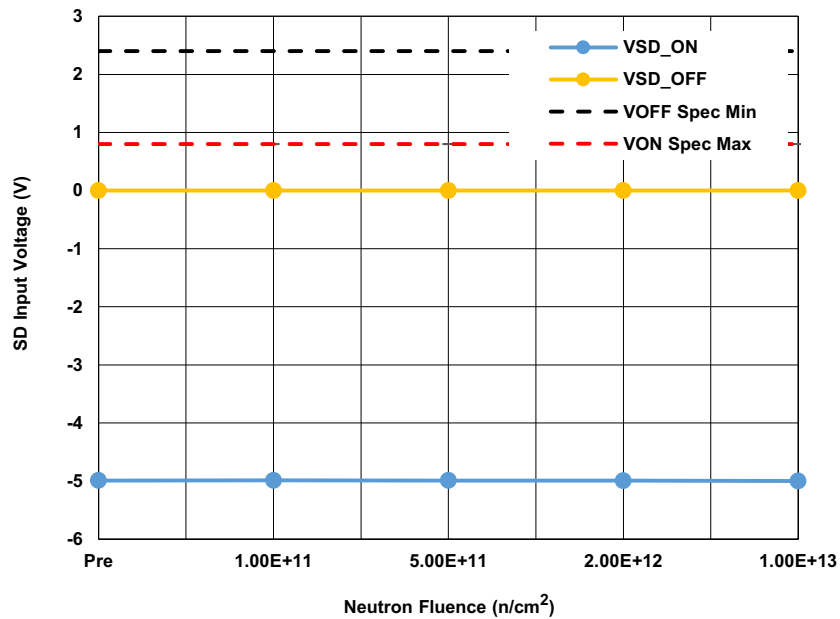


Figure 9. ISL72991RH shutdown input voltage (V_{SD}) at two different conditions following irradiation to each level. Parts were non-functional after $1\text{E}14\text{n/cm}^2$ and the results are not plotted. V_{SD_ON} denotes $V_O = \text{ON}$, and V_{SD_OFF} denotes $V_O = \text{OFF}$. The error bars represent the minimum and maximum measured values. The SMD limits are 0.8V maximum for V_{SD_ON} and 2.4V minimum for V_{SD_OFF} .

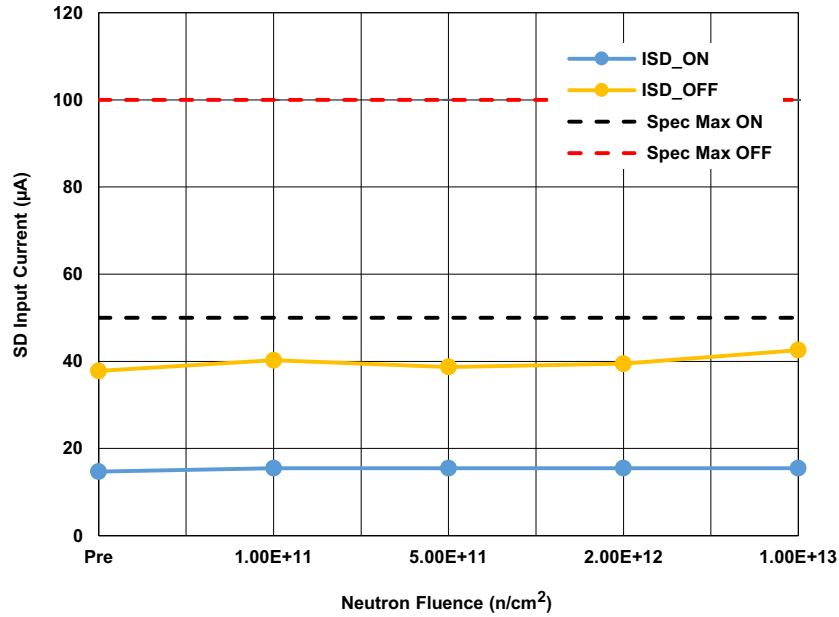


Figure 10. ISL72991RH shutdown input current (I_{SD}) at two different conditions following irradiation to each level. Parts were non-functional after $1E14n/cm^2$ and the results are not plotted. I_{SD_ON} denotes $V_{SD} = 0.8V$, and I_{SD_OFF} denotes $V_{SD} = 2.4V$. The error bars represent the minimum and maximum measured values. The SMD limits are $50\mu A$ maximum for I_{SD_ON} and $100\mu A$ maximum for I_{SD_OFF} .

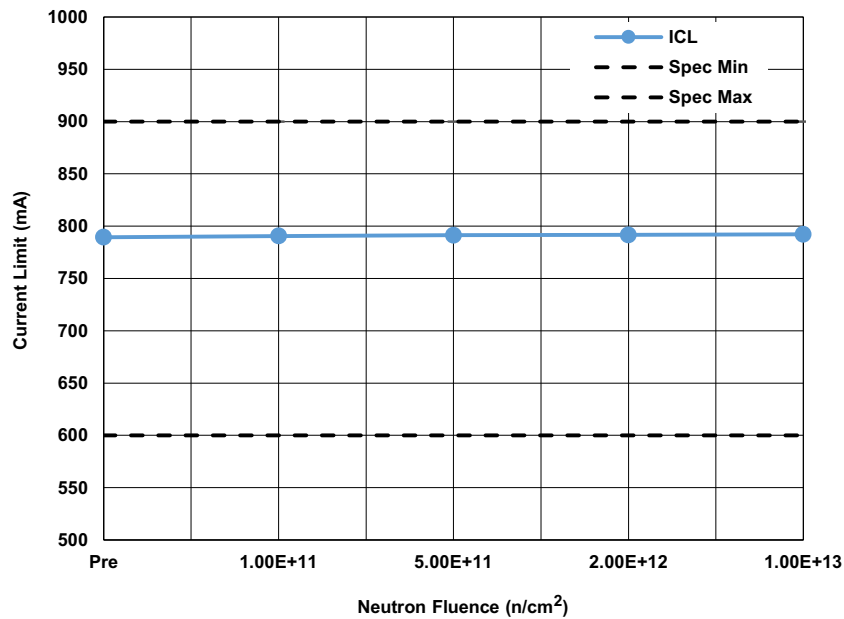


Figure 11. ISL72991RH current limit (I_{CL}), with $R_{CL} = 3.7k\Omega$ following irradiation to each level. Parts were non-functional after $1E14n/cm^2$ and the results are not plotted. The error bars represent the minimum and maximum measured values. The SMD limits are $600mA$ minimum and $900mA$ maximum.

3. Discussion and Conclusion

This document reports the results of 1MeV equivalent neutron testing of the ISL72991RH radiation hardened low dropout adjustable negative voltage regulator. Parts were tested at $1 \times 10^{11} \text{n/cm}^2$, $5 \times 10^{11} \text{n/cm}^2$, $1 \times 10^{12} \text{n/cm}^2$, $1 \times 10^{13} \text{n/cm}^2$, and $1 \times 10^{14} \text{n/cm}^2$. All samples passed the SMD limits after all exposures up to and including $1 \times 10^{13} \text{n/cm}^2$, but failed after $1 \times 10^{14} \text{n/cm}^2$. The results of key parameters before and after irradiation to each level are plotted in [Figure 1](#) through [Figure 11](#). The plots show the mean of each parameter as a function of neutron irradiation, with error bars that represent the minimum and maximum measured values. The figures also show the applicable electrical limits taken from the SMD.

4. Revision History

Date	Rev.	Description
1.00	May 28, 2026	<ul style="list-style-type: none">Applied latest template.Updated the Variables Data and Discussion and Conclusion sections.
0.00	Mar 21, 2018	Initial release

A. Appendix

Table 3. Reported Parameters

Figure	Parameter	Limit, Low	Limit, High	Unit	Notes
1	Reference Voltage	-1.279	-1.231	V	$3\text{mA} \leq I_O \leq 1\text{A}$, $V_O - 1.0\text{V} \geq V_{IN} \geq -30\text{V}$
2	Output Voltage Range	-	-2.25	V	$V_{IN} = -3.0\text{V}$, $I_O \leq 100\text{mA}$
3		-26.0	-	V	$V_{IN} = -30\text{V}$, $I_O \leq 100\text{mA}$
4	Load Regulation	-12	12	mV	$3\text{mA} \leq I_O \leq 1\text{A}$, $V_{IN} = -30\text{V}$, $V_O = -5\text{V}$
5	Line Regulation	-25	25	mV	$I_O = 100\text{mA}$, $V_O - 1.0\text{V} \geq V_{IN} \geq -30\text{V}$
6	Dropout Voltage	-	0.2	V	$I_O = 100\text{mA}$, $\Delta V \leq 50\text{mV}$
		-	1.0	V	$I_O = 1\text{A}$, $\Delta V \leq 50\text{mV}$
7	Adjust Current	-	5	μA	$I_O \leq 500\text{mA}$, $V_O - 1.0\text{V} \geq V_{IN} \geq -30\text{V}$
8	Dropout Quiescent Current	-	25	mA	$I_O \leq 500\text{mA}$, $V_O - V_{IN} = 0.2\text{V}$
9	SD Input Voltage	-	0.8	V	V_O : ON
		2.4	-	V	V_O : OFF
10	SD Input Current	-	50	μA	$V_{SD} = 0.8\text{V}$
		-	100	μA	$V_{SD} = 2.4\text{V}$
11	Current Limit	600	900	mA	$R_{CL} = 3.7\text{k}\Omega$

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